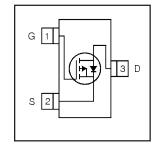


HEXFET® Power MOSFET

V _{DS}	-20	V
V _{GS Max}	±12	٧
$R_{DS(on) max}$ (@V _{GS} = -4.5V)	135	$\mathbf{m}\Omega$
$R_{DS(on) max}$ (@V _{GS} = -2.5V)	236	mΩ





Application(s)

• System/Load Switch

Features and Benefits

Features

Industry-standard pinout
Compatible with existing Surface Mount Techniques
RoHS compliant containing no lead, no bromide and no halogen
MSL1, Consumer qualification

Benefits

results in

Delicitio
Multi-vendor compatibility
Easier manufacturing
Environmentally friendly
Increased reliability

Absolute Maximum Ratings

Symbol	Symbol Parameter		Units
V _{DS}	Drain-Source Voltage	-20	V
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ -10V	-2.6	
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ -10V	-2.1	А
I _{DM}	Pulsed Drain Current	-11	
P _D @T _A = 25°C	Maximum Power Dissipation	1.3	10/
P _D @T _A = 70°C Maximum Power Dissipation		0.80	W
Linear Derating Factor		0.01	W/°C
V _{GS} Gate-to-Source Voltage		± 12	V
$T_{J,}T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Тур.	Max.	Units
R _{eJA}	Junction-to-Ambient ③		100	°C/W
$R_{\theta JA}$	Junction-to-Ambient (t<10s)		99	C/VV

ORDERING INFORMATION:

See detailed ordering and shipping information on the last page of this data sheet.

Notes ① through ④ are on page 10 www.irf.com

Electric Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-20		_	V	$V_{GS} = 0V, I_D = -250\mu A$
	Breakdown Voltage Temp. Coefficient		9.5		mV/°C	Reference to 25°C, I _D = -1mA
			90	135		V _{GS} = -4.5V, I _D = -2.6A ②
R _{DS(on)}	Static Drain-to-Source On-Resistance		157	236	mΩ	V _{GS} = -2.5V, I _D = -2.1A ②
V _{GS(th)}	Gate Threshold Voltage	-0.4		-1.1	V	$V_{DS} = V_{GS}$, $I_D = -10\mu A$
I _{DSS}	Durin to Common Lordon of Common			-1.0		$V_{DS} = -16V, V_{GS} = 0V$
	Drain-to-Source Leakage Current			-150	μΑ	$V_{DS} = -16V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			100		V _{GS} = 12V
	Gate-to-Source Reverse Leakage			-100	nA	V _{GS} = -12V
R _G	Internal Gate Resistance		16		Ω	
gfs	Forward Transconductance	3.4			S	$V_{DS} = -10V, I_{D} = -2.6A$
Q_g	Total Gate Charge		2.9			I _D = -2.6A
Q _{gs}	Gate-to-Source Charge		0.52		nC	V _{DS} =-10V
Q_{gd}	Gate-to-Drain ("Miller") Charge		1.2			V _{GS} = -4.5V ②
t _{d(on)}	Turn-On Delay Time		5.3			V _{DD} =-10V@
t _r	Rise Time		7.7			I _D = -1.0A
t _{d(off)}	Turn-Off Delay Time		26		ns	$R_G = 6.8\Omega$
t _f	Fall Time		16			V _{GS} = -4.5V
C _{iss}	Input Capacitance		220			V _{GS} = 0V
C _{oss}	Output Capacitance		70		pF	V _{DS} = -16V
C _{rss}	Reverse Transfer Capacitance		48			f = 1.0KHz

Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current			-1.3		MOSFET symbol
	(Body Diode)			-1.5	A	showing the
I _{SM}	Pulsed Source Current			-11	^	integral reverse
	(Body Diode) ①			-11		p-n junction diode.
V_{SD}	Diode Forward Voltage			-1.2	V	$T_J = 25^{\circ}C$, $I_S = -2.6A$, $V_{GS} = 0V$ ②
t _{rr}	Reverse Recovery Time		17	26	ns	$T_J = 25^{\circ}C$, $V_R = -15V$, $I_F = -2.6A$
Q _{rr}	Reverse Recovery Charge		6.2	9.3	nC	di/dt = 100A/μs ②

International **IOR** Rectifier

IRLML2246TRPbF

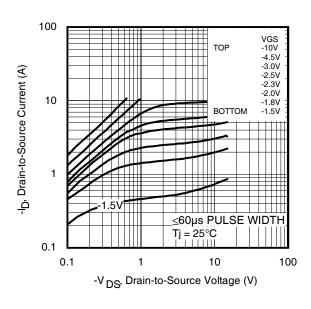
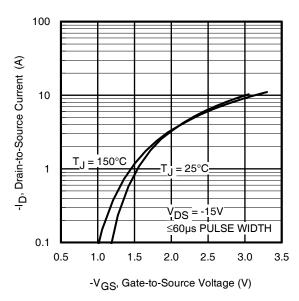


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics



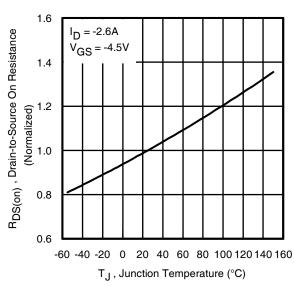


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

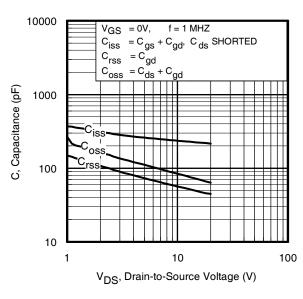


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

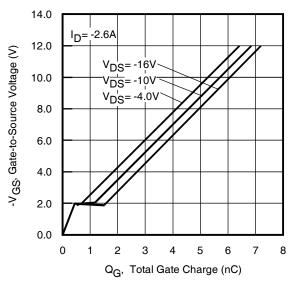


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

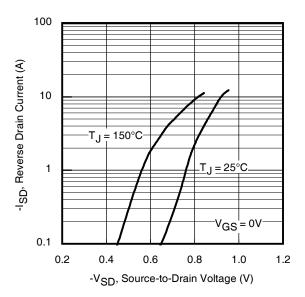


Fig 7. Typical Source-Drain Diode Forward Voltage

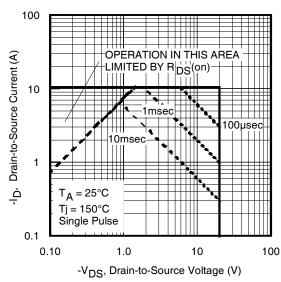


Fig 8. Maximum Safe Operating Area

International **IOR** Rectifier

IRLML2246TRPbF

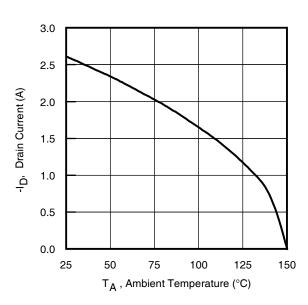


Fig 9. Maximum Drain Current vs. Ambient Temperature

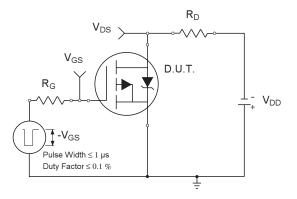


Fig 10a. Switching Time Test Circuit

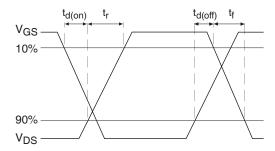


Fig 10b. Switching Time Waveforms

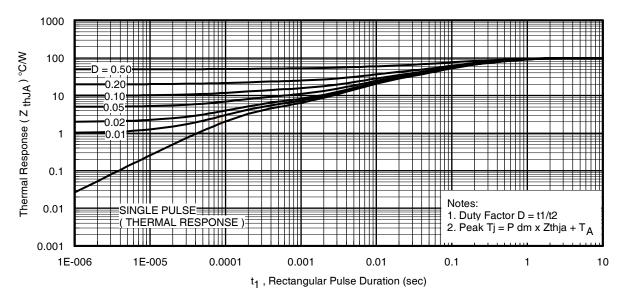
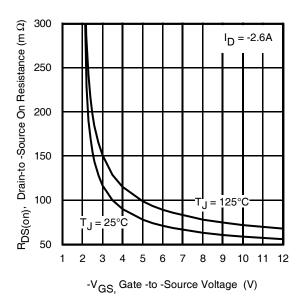


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient



Output 1000 Vgs = -2.5V Vgs = -4.5V Vgs =

Fig 12. Typical On-Resistance vs. Gate Voltage

Fig 13. Typical On-Resistance vs. Drain Current

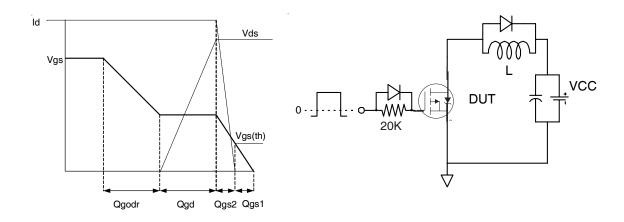
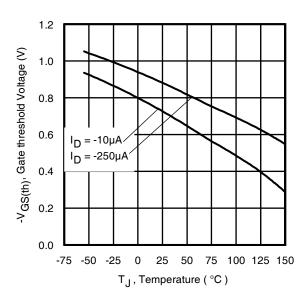


Fig 14a. Basic Gate Charge Waveform

Fig 14b. Gate Charge Test Circuit

International IOR Rectifier

IRLML2246TRPbF



1000 800 (M) Jawod esind 400 200 1E-7 1E-6 1E-5 1E-4 1E-3 1E-2 1E-1 1E+0 Time (sec)

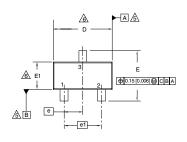
Fig 15. Typical Threshold Voltage vs. Junction Temperature

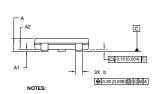
Fig 16. Typical Power vs. Time

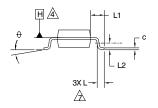
International IOR Rectifier

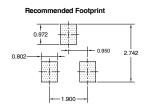
Micro3 (SOT-23) Package Outline

Dimensions are shown in millimeters (inches)









	DIMENSIONS				
SYMBOL	MILLIM	ETERS	INCH	HES	
STIVIBOL	MIN	MAX	MIN	MAX	
Α	0.89	1.12	0.035	0.044	
A1	0.01	0.10	0.0004	0.004	
A2	0.88	1.02	0.035	0.040	
b	0.30	0.50	0.012	0.020	
С	0.08	0.20	0.003	0.008	
D	2.80	3.04	0.110	0.120	
Е	2.10	2.64	0.083	0.104	
E1	1.20	1.40	0.047	0.055	
е	0.95	BSC	0.037	BSC	
e1	1.90	BSC	0.075	BSC	
L	0.40	0.60	0.016	0.024	
L1	0.54	REF	0.021	REF	
L2	0.25	BSC	0.010	BSC	
0	0	8	0	8	

- DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3. CONTROLLING DIMENSION: MILLIMETER.

 A DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
- ∠∆DATUM PLANE HIS LOCATED AT THE MICL D PARTINIS LINE.

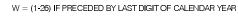
 ADATUM A AND B TO BE DETERMINED AT DATUM PLANE H.

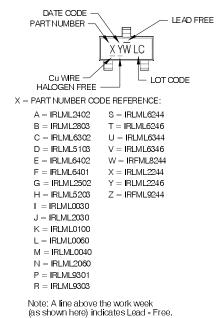
 ADMINISIONS D AND BI ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES
 NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD PLASH MICLD PROTRUSIONS
 OR INTERLEAD PLASH SHALL NOT EXCEED 0.25 MI/(10.010 INCH) PER SIDE.

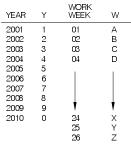
 ADMENSION, IS THE LEAD LEASH SHALL SOFT EXCEED 1.25 MI/(10.010 INCH) PER SIDE.

 B OUTLINE CONFORMS TO JEDEC OUTLINE TO 226 AB.

Micro3 (SOT-23/TO-236AB) Part Marking Information







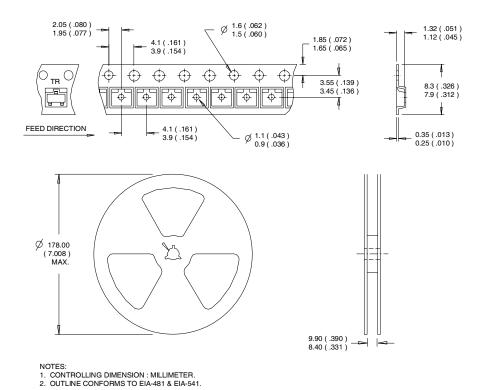
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Υ	WORK WEEK	W
2001	Α	27	Α
2002	В	28	В
2003	С	29	С
2004	D	30	D
2005	Е		
2006	F		
2007	G		
2008	Н		
2009	J	7	
2010	K	50	X
		51	Υ
		52	Z

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

Micro3™ (SOT-23) Tape & Reel Information

Dimensions are shown in millimeters (inches)



Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

International

TOR Rectifier

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRLML2246TRPbF	Micro3 (SOT-23)	Tape and Reel	3000	

Qualification information[†]

Qualification level	Consumer ^{††}		
	(per JEDEC JESD47F ^{†††} guidelines)		
Moisture Sensitivity Level	Micro (COT 00)	MSL1	
	Micro3 (SOT-23)	(per IPC/JEDEC J-STD-020D ^{†††})	
RoHS compliant	Yes		

- † Qualification standards can be found at International Rectifier's web site http://www.irf.com/product-info/reliability
- †† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: http://www.irf.com/whoto-call/salesrep/
- ††† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width \leq 400 μ s; duty cycle \leq 2%.
- ③ Surface mounted on 1 in square Cu board.
- Refer to <u>application note #AN-994.</u>

Data and specifications subject to change without notice.



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information, 01/2011